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and chemistry of surfaces and interfaces

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APPLIED SURFACE SCIENCE

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Editors

Professor F.H.P.M. Habraken
Debye Institute
Utrecht University
P.O. Box 80.000
3508 TA Utrecht
The Netherlands

Fax: +31-30-2535787
E-mail: f.h.p.m.habraken@phys.uu.nl

Professor J.E. Rowe
Physics Department
North Carolina State University
P.O. Box 8202
Raleigh, NC 27695-8202
USA

Fax: +1 919 515-6538
E-mail: rowe@unity.ncsu.edu

Professor H. Kobayashi
Editorial Office
Applied Surface Science
Institute of Scientific and Industrial Research
Osaka University
8-1 Mihogaoka, Ibaraki, Osaka 567-0047
Japan

Tel.: +81 6 6879 8450
Fax: +81 6 6879 8454
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Professor F.H.P.M. Habraken
Debye Institute
Utrecht University
P.O. Box 80.000
3508 TA Utrecht
The Netherlands

Fax: +31-30-2535787
E-mail:
f.h.p.m.habraken@phys.uu.nl

Professor J.E. Rowe
Physics Department
North Carolina State University
P.O. Box 8202
Raleigh, NC 27695-8202
USA

Fax: +1 919 515-6358
E-mail:
rowe@unity.ncsu.edu

Professor H. Kobayashi
Editorial Office
Applied Surface Science
Institute of Scientific and Industrial Research, Osaka University
8-1 Mihogaoka, Ibaraki
Osaka 567-0047
Japan

Tel.: +81 6 6879 8450
Fax: +81 6 6879 8454
E-mail: ass@sanken.osaka-u.ac.jp

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Institute of Applied Physics
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Raleigh, NC 27695-8202, USA

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75230 Paris Cedex 05, France

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Namiki, Tsukuba, Ibaraki 305-0044, Japan

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Gaithersburg, MD 20899, USA

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Pittsburgh, PA 15260, USA

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Editors:
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Biological materials
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Electron spin resonance
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Ellipsometry
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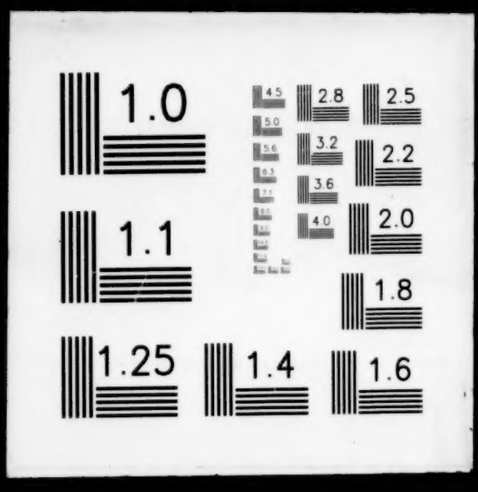
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